

MAEBL

MEETING FOR ADVANCED E-BEAM LITHOGRAPHY

MAEBLx Asia Pacific
July 29, 2022, 2-4 PM AEDT

MAEBL at Caltech
September 14-15, 2022

MAEBLx Europe
November 15, 2022, 3-5 PM CET

2022 Program

www.maabl.org • Online + In-person September 14-15, 2022
California Institute of Technology

Details and registration: maabl.eventbrite.com

Dear Colleagues:

We are delighted to invite the entire electron beam lithography community to the **6th Meeting for Advanced Electron Beam Lithography**, affectionately known as MAEBL. Last year, 80 registered attendees spanning eight countries (Australia, Canada, France, India, Saudi Arabia, Switzerland, the United Kingdom and the United States) participated in the meeting's two-day event to discuss best practices, common challenges, and state-of-the-art techniques for fine feature patterning in EBL. The fluid situation brought by the pandemic reminds us to remain flexible and therefore function as a hybrid (in-person and online) meeting.

This year, the **California Institute of Technology** (Caltech) will host the hybrid meeting on **September 14-15, 2022**. Included in this year's registration in addition to the hybrid meeting is a drop-shipped t-shirt and two MAEBLx meetings for Asia Pacific and Europe, which will take place on July 29, 2022, 2:00 pm - 4:00 pm AEST (12:00 am - 2:00 am EDT) and in November 15, 2022 (9:00 am - 11 am EDT), respectively. The registration cost is the same for in-person and online attendees. We hope you will take advantage of this opportunity to meet with users from around the world.

As always, we are indebted to our sponsors whose support offsets costs for the venue, t-shirts, food/beverage, registration assistance, and other services. Without their support, MAEBL could not continue to grow and reach as many attendees. In our 6th meeting, we are humbled by the overwhelming appreciation and support we received from the entire community.

We look forward to seeing you online and in person soon.

Sincerely,
The MAEBL Steering Committee

Aimee Price, President, The Ohio State University
Mark Mondol, Vice President, Massachusetts Institute of Technology
Mason Risley, Secretary, Carnegie Mellon University (former)
Gerald Lopez, Board Chair & Treasurer, The University of Pennsylvania
Guy Derose, California Institute of Technology
Justin Wirth, Purdue University



Thank you sponsors!





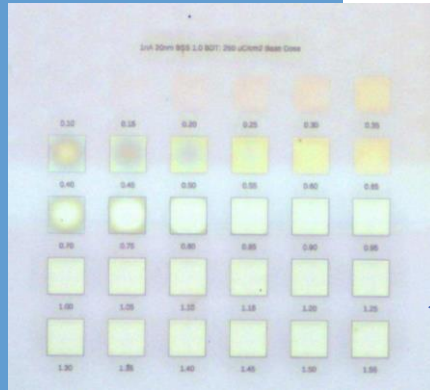
DisChem

CHEMISTRY FOR ADVANCED LITHOGRAPHY

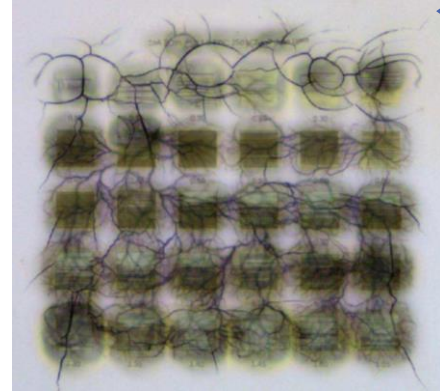
DisCharge H2O

EBL ANTI-CHARGING AGENT

- Improved shape fidelity and positional accuracy for EBL resist patterning on insulating substrates such as fused silica, quartz, glass, PDMS, etc.
- Water based w/ excellent wetting properties. Spin coat application provides conductive film for anti-charging.
- Suitable for nondestructive SEM imaging of nonconductive materials.
- Easy residue free removal w/ water or IPA.
- Competitively priced. Ideal for both research and industrial applications.
- Two-year shelf life at room temp. Highly stable permanently charged non-polymer formulation.
- Ready to use. No filtration required prior to use.



anti-charging



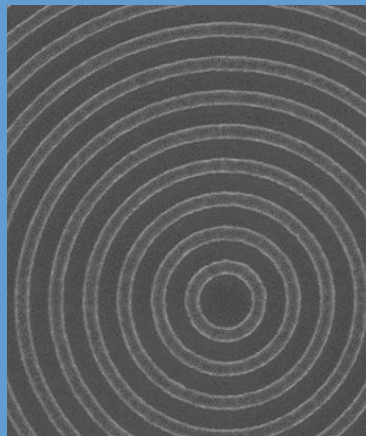
Without DisCharge: charge accumulation and sudden charge dissipation caused by exceeding the dielectric strength of the PDMS to the Si substrate resulting in significant image distortion in the resist and destruction of the PDMS surface.

WITH DisCharge: no charge accumulation, resulting in expected image with no harm to PDMS layer.

H-SiQ (hydrogen silesquioxane)

NEGATIVE-TONE ELECTRON BEAM RESIST

DisChem H-SiQ is a negative tone hydrogen silesquioxane (HSQ) resist in MIBK carrier solvent for use in electron beam lithography (EBL). H-SiQ is characterized by excellent pitch resolution, sensitivity and etch resistance for direct write thin and thick film EBL applications. Immediate availability in quantities as low as 20 ml.



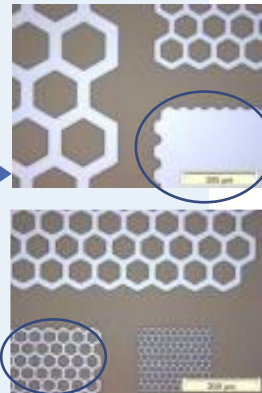
resist

SurPass

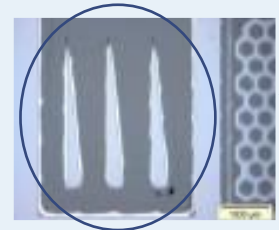
RESIST ADHESION PROMOTERS

- Improved microlithographic resist adhesion on a broad range of substrate materials.
- Improved adhesion at low doses in electron beam lithography
- Improved removal of critical substrate contaminants
- Reduced z-potential for improved resist coating properties
- Improved patterned resist mold to copper seed layer for subsequent electroforming.
- Increased adhesion of evaporated metals to substrate materials
- Non-Hazardous waterborne formulation

No Adhesion Promoter: some patterns removed during resist development



▲With SurPass: Complete Precision Mask



◀No Adhesion Promoter Resist Mask Undercut During Etching

With SurPass: Complete Precision Mask



adhesion promotion



ALLRESIST

Company for Chemical Products
for Microstructuring

Conductive Resist Electra 92

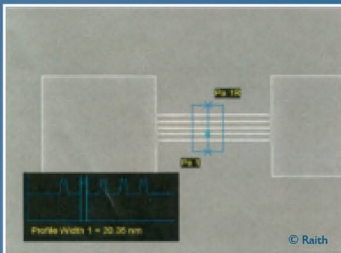
Charge dissipation, for Excellent nanostructures, top-layer for e-beam resists, easy removal with water.

Electra 92 on different e-beam resists and insulating substrates:

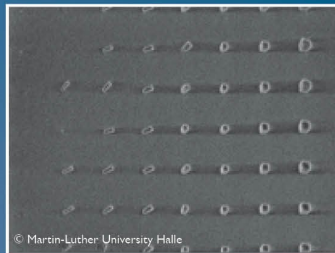
Positive E-Beam Resist CSAR 62

High resolution, highly sensitive, excellent plasma etch resistance, improvement to ZEP-resists

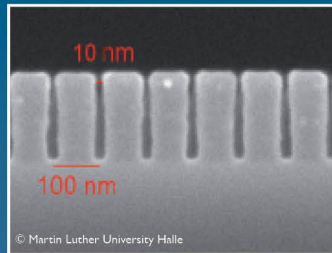
Excellent resolution at 10 nm dose to clear: $10 \mu\text{C}/\text{cm}^2$ resist thickness: up to $1.5 \mu\text{m}$



20 nm lines of HSQ, generated on quartz with Electra 92



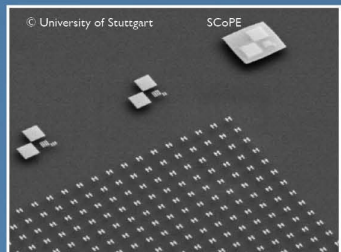
60 – 150 nm squares (height 100 nm) with AR-N 7700.08 / Electra 92 on glass



Spacing with an aspect ratio of 18; 10 nm resolution at a film thickness of 180 nm



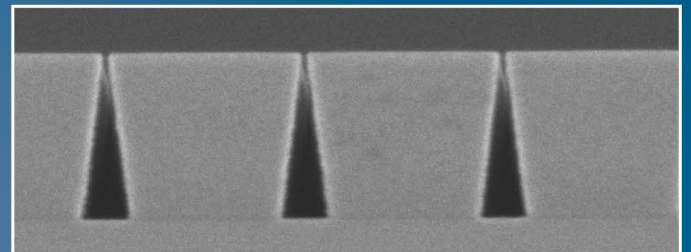
Well-defined 3D resist profile for a T-gate nanostructure with 950k PMMA (bottom) / AR-P 617 / CSAR 62



Strongly isolating polymer structures coated with Electra 92 in SEM



30 – 150 nm squares with CSAR 62 and Electra 92 on glass

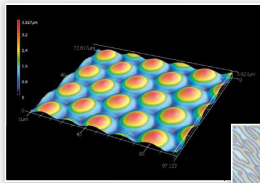


Forming of lift-off structures with CSAR 62 at higher dose

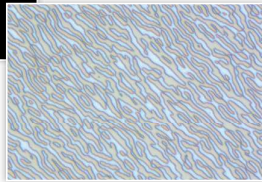
System Solutions

From Micro- to Nanofabrication

LASER

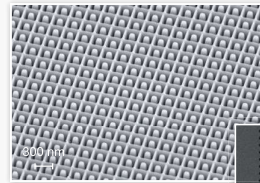


Grayscale
Lithography

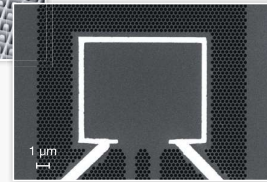


Augmented/
Virtual Reality

FIB

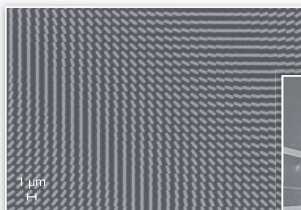


Metasurfaces

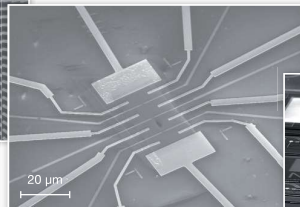


Phononic
Engineering

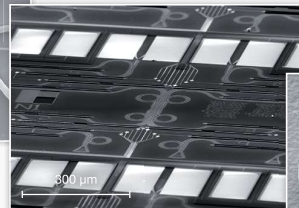
E-BEAM



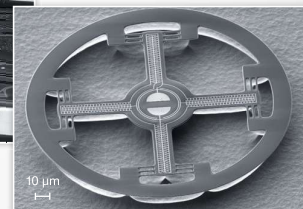
Photonics



Nanoscale
Science



Quantum
Technologies



Electro-Optomechanics

H.A.R.P PMMA

High Aspect Ratio PMMA for e-beam



MicroVision Labs: 100nm, 600µC, holes
MAG: 20.0kx

SHORT LEAD TIMES

COMPETITIVE PRICING

SOURCED & SHIPPED IN USA

Resist Type

If you are currently using...

Use this KemLab Resist Series

Negative Permanent Epoxy

SU-8™

HARE SQ™
IMPROVED TRANSPARENCY

Thick Positive Advanced Packaging

AZ® P4620
SPR™ 220-7.0

K-PRO™
EXCELLENT PROCESS LATITUDE

Negative Lift-Off

AZ® nLOF™ 2000

APOL-LO 3200
PATENT PENDING • WIDER PROCESS LATITUDE

Positive FT: 0.5-2.0 µm

MICROPOSIT™ S1800™
AZ® 1500

KL 5300
DESIGNED FOR IC FABRICATION • HIGH RESOLUTION

Positive FT: 2.5-12 µm

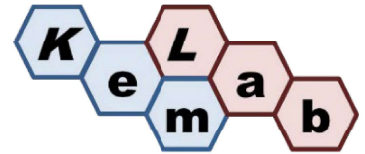
SPR™ 220 Series
SC1827™

KL 6000
DESIGNED FOR THICK FILMS • VALUE RESIST

High Resolution e-Beam Positive

950K / 495K PMMA
MMA (8.5) MAA

HARP™ PMMA
DIRECT WRITE E-BEAM



PHOTORESIST
MANUFACTURING & INNOVATION

H.A.R.E SQ Negative Epoxy

High Aspect Ratio Epoxy with Superior Quality

BETTER OPTICAL TRANSPARENCY

SUPERIOR RAW MATERIALS

DESIGNED FOR MICROELECTRONICS



ELS-BODEN

Electron Beam Lithography System

ELIONIX
Action for innovation



ELS-BODEN

Acceleration 100kV × Single autoloader

High Performance Capabilities for High Resolution and High Throughput Applications

Features

Inherits traditional Elionix technology to meet user's requirements:

- 150kV / 125kV acceleration voltages, if ultra-fine patterns are most important.
- 100kV for common applications and a wide variety of requirements.
- 50kV for high speed production.


Available in 200mm and 300mm chambers:

- The first full 300mm square writing area in the marketplace.
- Sample holders from small pieces commonly used in basic research to 300mm wafers.
- Mask holders, for the 6025 and 9025 mask sizes, are also available.

Complete line of automatic loading systems:

- Single cassette autoloader, which is useful for research and development applications.
- Multiple cassette autoloader for small to medium volume production.
- Full lineup of robot loading systems

Specifications

Electron Gun	ZrO/W Thermal Field Emitter			
Acceleration voltage	50kV	100kV	125kV	150kV
Beam current	1nA ~ 800nA	20pA ~ 100nA	5pA ~ 100nA	5pA ~ 100nA
Min. beam spot size	D5nm	D1.8nm	D1.7nm	D1.5nm
Writing field size	1000μm□	1000μm□	500μm□	500μm□
Min. / Max. Field size	Min 100μm square Max (Option) 3000μm square			
Scan clock	Max 200MHz			
Min. beam position	0.1nm (at standard field)			
Max. sample size	200mm wafer / 300mm wafer			
Max. writing area	200mm square / 300mm square			
Loading system	Single autoloader Multi autoloader 300mm FOUNDRY robot loader PEB robot loader			
Software	 Beam conditions Exposure schedule Pattern data converter Account management Python scripting			

MAEBL Community Conduct Expectations

MAEBL is committed to providing a safe and inclusive community environment for professional networking, an open exchange of EBL related experiences and ideas, and mutual learning and education.

In order to maintain a welcoming space and community, the following types of conduct are not tolerated at MAEBL meetings, at gatherings related to MAEBL meetings, or in MABEL community platforms:

- Harassment: unwelcome conduct that undermines a safe and inclusive community environment, especially based on factors of a person's identity unrelated to MAEBL's mission.
- Sexual harassment: unwelcome romantic or sexual advances, behavior, or comments.
- Discrimination: exclusion of a person based on factors of a person's identity unrelated to MAEBL's mission.
- Retaliation: punitive treatment of a person for bringing attention, in good faith, to conduct that undermine a safe and inclusive community environment.

Acts of harassment, sexual harassment, discrimination, or retaliation are encouraged to be reported to a member (or members) of the MAEBL board, will be taken seriously, and will be investigated.

Substantiated instances of conduct contrary to community expectations will be handled by members of the MAEBL board addressing and challenging the conduct with the transgressing person and explaining conduct expectations. It is expected that the person will change future conduct to be mindful of and consistent with community expectations.

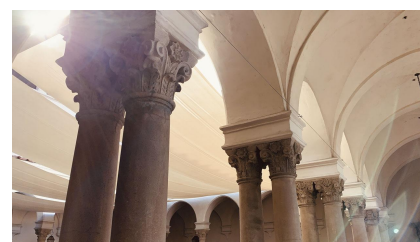
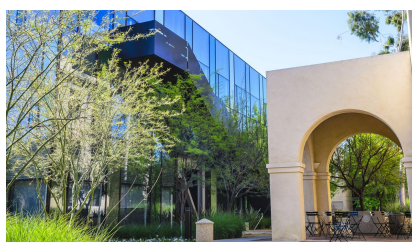
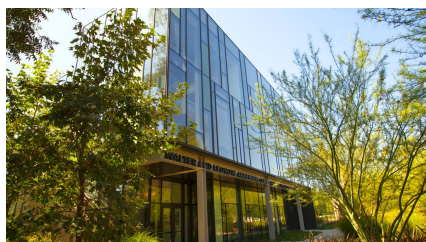
Repeated, bad faith, or exceptionally serious conduct may necessitate exclusion from the community for an appropriate period of time. Bad faith claims are themselves considered to be harassment; good faith claims that are not substantiated are not considered harassment and are protected from retaliation.

REGISTRATION and QUALIFICATIONS TO REGISTER

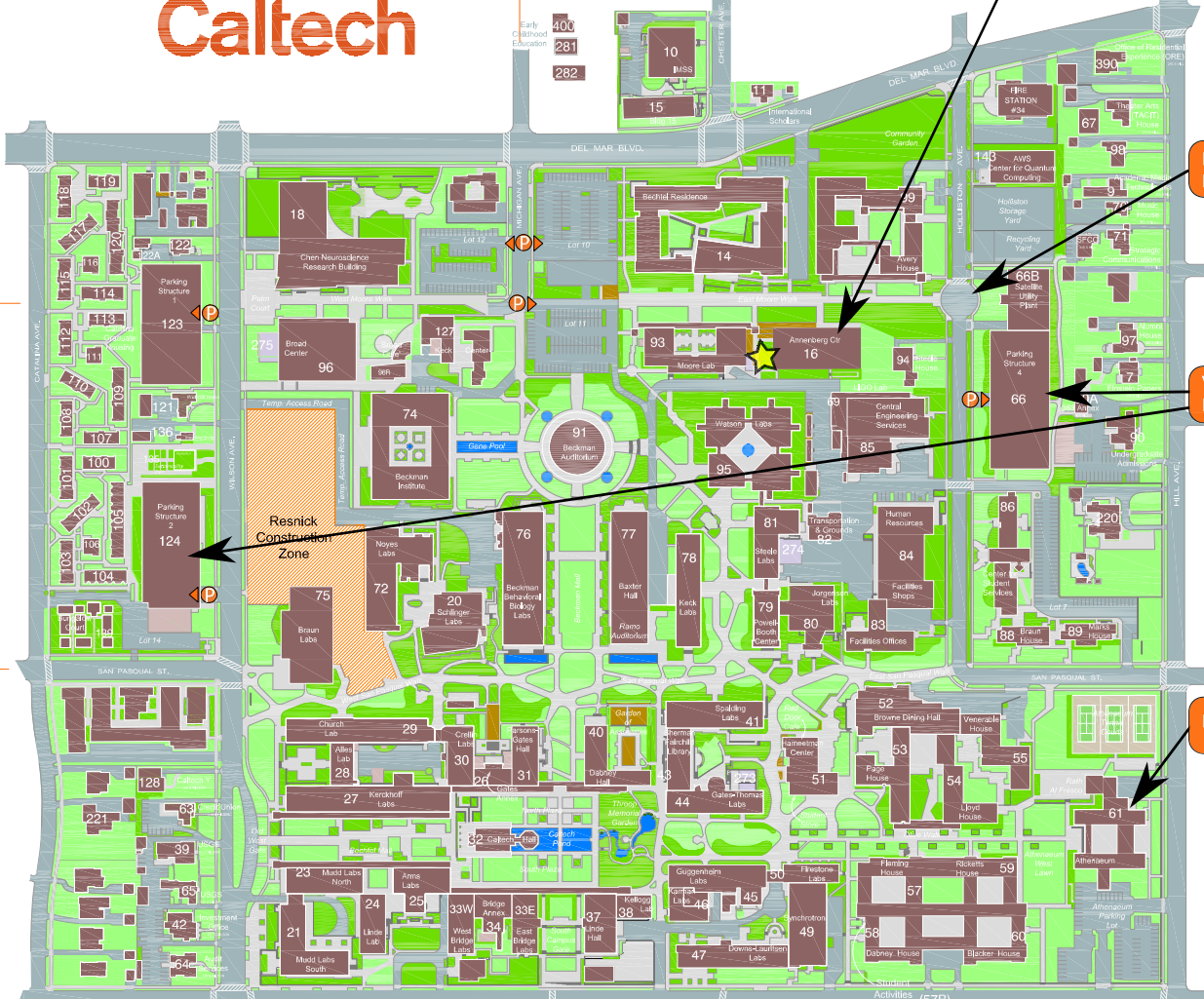
Registration helps to offset the operational costs of the meeting series. All active EBL tool owners and users from academic, industrial, or government institutions/organizations are encouraged to attend. To promote intimate dialogue, we have kindly requested that EBL hardware vendors refrain from registering. Automatic attendance is granted to organizers, speakers, and non-EBL-hardware vendor sponsors. Advance online sign-up is required to participate as there will be no on-site registration. This year Caltech is permitting up to 50 in-person attendees to be on campus. Please see <http://together.caltech.edu/> for further guidance for on-campus participation. Please be mindful that we are a volunteer operated non-profit organization. **A single registration is for an individual, not an organization, and is not transferable.** Anyone wishing to attend must register under their own name. An attempt to transfer registration undermines our mission and capacity to organize meetings for the international electron beam lithography community.

Attendee Registration Type	Description	Cost
Full Registration (Virtual or In-Person)	All access to MAEBL 2022 at Caltech, MAEBLx Asia-Pacific and MAEBLx Europe. One t-shirt is included in the cost.	\$165 per attendee online or in person
Registration for MAEBLx Only	Access to one MAEBLx meeting only. Additional access to MAEBL 2022 at Caltech is the cost of a Full Registration (\$165) should you decide to attend at a later date. No t-shirt.	\$45 per attendee for one MAEBLx Meeting
Invited Speakers	All access to MAEBL 2022 at Caltech, MAEBLx Asia-Pacific and MAEBLx Europe. One t-shirt is included.	Free
Vendor Sponsorship	Logo on T-shirt, website, and other collateral material including a one page ad in the MAEBL 2022 program.	\$500 per vendor

Register at maebl.eventbrite.com



Caltech

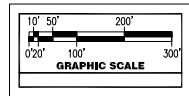
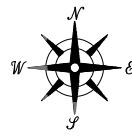


Resnick Construction Zone

Ride/Share Drop-off

Visitor Parking

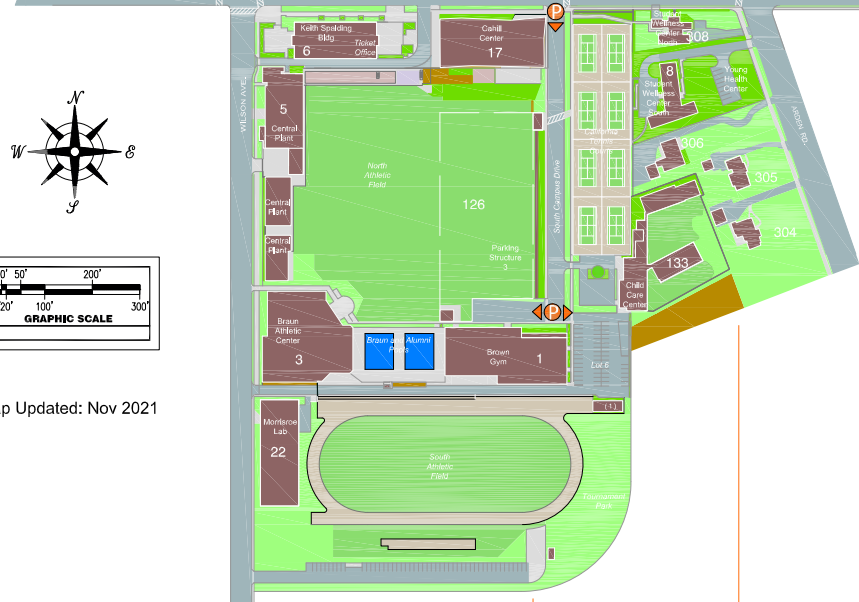
Banquet



Map Updated: Nov 2021

Map Key

- Campus Building
- Building Name
- Building Number
- Athletic Track or Court Area
- Crosswalk
- Paved Walkway or Pedestrian Area
- Paved Driveway or Street
- To Parking
- Place Name
- Utility Pad
- Utility Grating
- Walls or Exterior Stairs
- Water Features or Pools
- Ground Cover: Lawn
- Ground Cover: Other Plants
- Ground Cover: Playing Field
- Ground Cover: None
- Under Construction



COVID-19 POLICY

The health and safety of the MAEBL community are our primary concern. Caltech's policies for on campus engagement are outlined at <http://together.caltech.edu/>. If you are attending in person, Caltech requires each attendee to be fully vaccinated and boosted. Everyone must be ready to show proof of vaccination upon request. Again, this means an in-person attendee:

1. completed a second dose in a 2-dose series (Pfizer or Moderna vaccine) or a single-dose vaccine (Johnson & Johnson) and
2. is 2 weeks after receiving a booster.

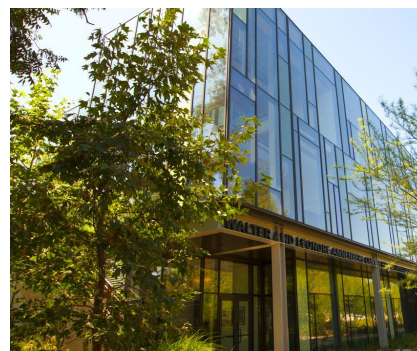
All attendees are required to wear a face-covering regardless of vaccination status. In the event of contact tracing, your information may be shared with the MAEBL Board, host, or any other responsible entities.

HOTELS

Since there are not enough in person attendees to reserve room blocks at a particular hotel, we are recommending the Hilton Pasadena or Sheraton Pasadena. There are of course other hotels and motels (Vagabond and Saga Inns) that are within walking distance.

MEETING VENUE

The meeting location is the **Walter and Leonore Annenberg Center for Information Science and Technology** (building #16), on the northeast side of campus. It's a large green glass building, so it's hard to miss. The best entry point for MAEBL attendees is the west side of Annenberg; look for the MAEBL program poster outside the building. The yellow star indicates the entry closest to the Auditorium (room #105).



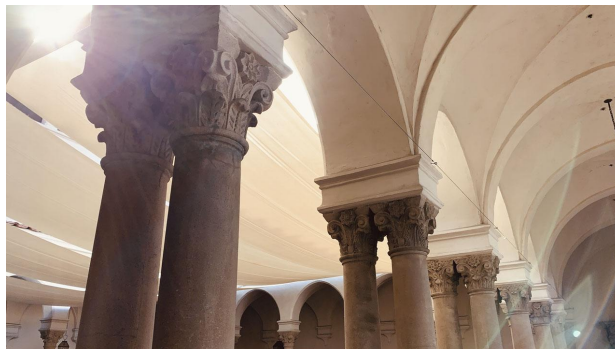
BANQUET VENUE

The Athenaeum (building #61 at the bottom right portion of the map) hosts our annual banquet at 6:30 pm PDT on September 14, 2022. The banquet is included in the registration for all In-person attendees and is made possible by the generous donations of our sponsors. Please note the Athenaeum [dress code](#) is business casual, e.g. dress shirts, slacks, blouses, leather shoes, etc.; no blue jeans and sneakers. Male guests must wear jackets. Business casual as defined by Wikipedia can be found [here](#). To repeat:

- [Dress code](#) is business casual.
- Not allowed: blue jeans, sneakers, shorts, casual/beach-wear sandals and flip-flops.
- ~~Males must wear jackets~~; coat and tie are always appropriate. Coat is not required.
- Proper attire includes the option of wearing collared shirts with dress slacks, suits, dresses, or dressy blouses/shirts with skirt or pants.
- Shoes are required throughout The Athenaeum and should be clean and appropriate for the occasion.

ARRIVAL BY RIDE SHARE

For Uber/Lyft/ride share, participants should get dropped off at the Holliston Ave circle. Participants arriving by ride share can be dropped off at the "round about" on South Holliston shown on the map as "Drop off". Walk down the main pathway (East Moore Walk) and turn left (south) at the small walkway between Annenberg and Moore.



PARKING

Parking information for visitors can be found at: <https://parking.caltech.edu/parking-info/visitor-parking>.

The closest parking is Parking Structure #4 (building 66 on the map) on South Holliston Avenue in any unnamed space. Parking is \$6 day using the kiosk on the second level. Parking Structure #2 (building 124) on South Wilson Avenue is also an option. Avoid parking spots designated as carpool or named parking spaces reserved for the permit holder's exclusive use.

REFUND and REGISTRATION TRANSFER POLICY

No refunds will be issued. Please be mindful that we are a volunteer operated non-profit organization. **A single registration is for an individual, not an organization, and is not transferable.** Anyone wishing to attend must register under their own name. An attempt to transfer registration undermines our mission and capacity to organize meetings for the electron beam lithography community. Thank you for your cooperation and understanding of this matter.

VIDEO RECORDING POLICY

To encourage attendance and participation, there is no video recording of the MAEBL meetings. We do this to respect the privacy and confidentiality of the opinions shared in our open discussions.

PRIVACY POLICY

In the event of contact tracing, your contact information may be shared with the University or any other responsible entities. For all other purposes, your registration information will not be distributed without your consent.

MAEBLx Europe (Online only)

November 15, 2022 (CET): MAEBLx Europe is scheduled to allow regional attendees to participate during a reasonable hour in their respective time zone. Major participating timezone hours are listed.

PST	EST	CET	AET	Topic	Facilitator
05:00	08:00	14:00	22:00	Connect to GatherTown + Online Networking	
06:00	09:00	15:00	23:00	Welcome, Opening Remarks and MAEBLpedia (www.maabl.org)	
06:20	09:20	15:20	23:20	EFFECTIVE BLUR Connecting the Process Window to the Effective Blur	Gerald Lopez University of Pennsylvania
07:05	10:05	16:05	00:05	COLD DEVELOPMENT A Discussion on the Setup and Process	Mark Mondol Massachusetts Institute of Technology
07:50	10:50	16:50	00:50	Closing Remarks	
08:00	11:00	17:00	01:00	Adjourn	

Abstracts

Connecting the Process Window to the Effective Blur

Scaling limits in electron beam lithography (EBL) are physically connected to the tooling, environment, pattern density, resist resolution, and downstream processes. In this talk, we'll discuss steps to characterize an EBL resist process and a high-level overview of the theory connecting the resist process window to the effective blur. We'll show how environmental factors like temperature can influence exposure latitude and present techniques in determining the effective blur will be demonstrated.

Cold Development: Setup and Process

Cold process development in EBL has long been shown to improve contrast and overall lithographic fidelity. Previous work has demonstrated cold development for both PMMA and ZEP520A. In this talk, we'll discuss equipment that worked and that didn't work for a new setup to support cold process development at MIT.nano including model numbers and cost.

MAEBLx Asia Pacific (Online only)

July 29, 2022 (AEDT): MAEBLx Asia Pacific is a regionally organized online event held at an appropriate hour in the regional time zone. All are welcome to attend. Major participating timezone hours are listed.

PDT	EDT	CEDT	AEDT	Topic	Facilitator
20:00 (July 28)	23:00 (July 28)	05:00 (July 29)	13:00 (July 29)	Online Networking	
21:00 (July 28)	00:00 (July 29)	06:00 (July 29)	14:00 (July 29)	Welcome, Opening Remarks and Announcements	
21:15	00:15	06:15	14:15	TEST PATTERNS A Comprehensive Performance Test Mask for EBL	Michael Stuiber Melbourne Centre for Nanofabrication
22:00	01:00	07:00	15:00	EMF CANCELLATION A Ghost Hunting Story in the EBL Facility	Elliot Cheng & Ron Rash Centre for Microscopy and Microanalysis, The University of Queensland
22:45	01:45	07:45	15:45	Closing Remarks	
23:00 (July 28)	02:00 (July 29)	08:00 (July 29)	16:00 (July 29)	Adjourn	

Abstracts

A Comprehensive Performance Test Mask for EBL

The Melbourne Centre for Nanofabrication (MCN) owns the largest open access cleanroom environment in the Southern Hemisphere. It is home to many state of the art micro- and nanofabrication tools which are heavily utilised by all 6 major Universities located in Melbourne and by MCN staff members. It is also home of the first 100 keV EBL system installed in Australia, a Raith (formerly Vistec) 5000plus tool.

Due to Australia's remoteness (difficult to bring an EBL service engineer) and the EBL tools large user cohort with a broad range of applications a need arose to monitor the tool performance and critical parameters in between service engineer visits or after software updates.

In this presentation, I will share the development process of the performance test mask, the ideas behind some of the test patterns and show some exposure results. Since this mask was specifically designed to be used on a Raith (formerly Vistec) tool with 1 mm² main field size I will try to present ways how to alter the mask to be used on other systems such as Elionix or JEOL.

A Ghost Hunting Story in the EBL Facility

Electron beam lithography instruments rely on the use of high precision electromagnetic and electrostatic systems to control the beam quality and deflection for long hours of writing. Any presence of Electron Magnetic Field (EMF) above the accepted noise threshold at various frequencies could have detrimental effects towards the quality of the final lithography patterns. Since the refurbishment of our new microscopy centre we have noticed several types of defects during our routine fabrication in the cleanroom. We have undergone a long journey to survey and pinpoint (ghost hunting) potential EMI sources around the building, leading to the installation of a new double coil EMF cancellation system inside the cleanroom. In this talk we will share our experience in finding common source of noises, the required instrumentation and techniques using for field detector, as well as establishing a test set up and the installation of an EMF cancellation system.

Session I: MAEBL Foundations Workshop*

September 14, 2022 (PDT): All e-beam lithographers are invited to participate in Session I to learn, brush-up or to mentor others on EBL fundamentals. Advanced attendees are encouraged to impart personal accounts and challenges to the audience to elevate the workshop experience. At the end of the meeting beginners should be conversant in EBL and are encouraged to participate in Session II.

PDT (Sept 14)	EDT (Sept 14)	CEDT (Sept 14)	AEDT (Sept 15)	Topic	Facilitator
09:00	12:00	18:00	02:00	Registration, Networking, Coffee and Light Breakfast	
09:30	12:30	18:30	02:30	Welcome, Opening Remarks and Speaker Introductions	
10:00	13:00	19:00	03:00	EBL TOOL ANATOMY Tool vendors, the tools and their terminology	Mason Risley Carnegie Mellon University (former)
10:45	13:45	19:45	03:45	SPECIFICATIONS AND WHAT THEY MEAN Stitching, Overlay, Placement Accuracy, etc.	Mark Mondol Massachusetts Institute of Technology
11:30	14:30	20:30	04:30	PATTERN & DESIGN FUNDAMENTALS Data Volume, Hierarchy, Shot Grid Placement, etc.	Gerald Lopez University of Pennsylvania
12:00	15:00	21:00	05:00	Group Photo, GatherTown Networking, Lunch	
13:15	16:15	22:15	06:15	PROXIMITY EFFECT CORRECTION What Is It, How It Works and When You Need It	Marvin Zai GenISys, Inc.
13:40	16:40	22:40	06:40	RESIST PROCESSES (PMMA, ZEP520A, HSQ, etc.) Baseline Processes + Spin Curve Fundamentals	Allison Dove [♦] & Leo Ocola [♣] [♦] University of California, Berkeley [♣] IBM T.J. Watson Research Center
14:40	17:40	23:40	07:40	Coffee Break/Continued Discussion and Networking	
15:10	18:10	00:10 (Sept 15)	08:10	PATTERN TRANSFER Nanopattern Transfer Using Reactive Ion Etching	Nikhil Tiwale Brookhaven National Laboratory
15:40	18:40	00:40	08:40	Break/Continued Discussion and Networking	
16:00	19:00	01:00	09:00	Breakout: General Q&A Session <ul style="list-style-type: none"> Resist Processes / Anti-Charging Pattern Transfer: Deposition and Etch Considerations / Lift-Off Processes Data Preparation and Proximity Effect 	
17:15	20:15	02:15	10:15	Breakout Summary	
17:30	20:30	02:30	10:30	End MAEBL Foundations	

*Program is subject to change without notice.

Session II: MAEBL Core*

September 15, 2022 (PDT): The meeting that started it all. Engage the EBL community's collective knowledge.

PDT (Sept 15)	EDT (Sept 15)	CEDT (Sept 15)	AEDT (Sept 16)	Topic	Facilitator
08:30	11:30	17:30	01:30	Networking, Coffee and Light Breakfast	
09:00	12:00	18:00	02:00	Welcome, Opening Remarks and Announcements	
09:30	12:30	18:30	02:30	RESIST PROCESSING An Interactive Survey with Mentimeter	Aimee Price The Ohio State University
09:45	12:45	18:45	02:45	RESIST PROCESSING Why I Hate PMMA and You Should Too	Allison Dove University of California, Berkeley
10:15	13:15	19:15	03:15	Coffee Break/Continued Discussion and Networking	
10:30	13:30	19:30	03:30	PATTERN TRANSFER Enhancing Etch Selectivity with Infiltration Synthesis	Nikhil Tiwale Brookhaven National Laboratory
11:00	14:00	20:00	04:00	PATTERN & DESIGN CONSIDERATIONS Orderings, Split and Bury, Bulk-Sleeve, Multipass, etc.	Gerald Lopez University of Pennsylvania
11:20	14:20	20:20	04:20	Quick Coffee Break	
11:30	14:30	20:30	04:30	COMMON CHALLENGES I An Open Forum Discussion of Common Issues	Justin Wirth [†] & Venkatachalam P [‡] [†] Purdue University [‡] India Institute of Science
12:30	15:30	21:30	05:30	Group Photo, GatherTown Networking, Lunch	
14:00	17:00	23:00	07:00	3D STRUCTURES Ternary Developer + Trilayer Process Enabled T-Gates	Leonidas Ocola IBM T.J. Watson Research Center
14:30	17:30	23:30	07:30	ALIGNMENT User-defined Joy Markers	Ivan Milosavljevic HRL Laboratories
15:00	18:00	00:00 (Sept 16)	08:00	Coffee Break/Continued Discussion and Networking	
15:15	18:15	00:15	08:15	TEST PATTERNS Drift within Mainfiled and In-field Alignment (Performance Test Part II)	Michael Stuber Melbourne Centre for Nanofabrication
16:15	19:15	01:15	09:15	COMMON CHALLENGES II Open Forum Discussion of Common Issues	Guy Derosé California Institute of Technology
17:15	20:15	02:15	10:15	Closing Remarks - Continued Discussion and Networking	
18:00	21:00	03:00	11:00	End MAEBL Core	

*Program is subject to change without notice.

Board of Directors

The Founders and Board Members



Aimee Bross Price (MAEBL Co-Founder, President, and Board Member) is the Manager for Nanofabrication at The Ohio State University Nanotech West Lab. She joined Ohio State in 2005 as a Senior Research Associate responsible for electron beam lithography (EBL). She has been a Member of Technical Staff with the Institute for Materials Research (IMR) since its inception. She has extensive experience in semiconductor device fabrication, nanofabrication, process development, and process design and troubleshooting. Aimee is passionate about training the next generation of technology experts and believes that encouraging and motivating K-12 students is crucial for continued growth in the field (and it is really fun). Aimee is the 2022 and 2023 Commercial Session Chair for the International Conference on Electron, Ion and Photon Beam Technology and Nanofabrication (EIPBN). She is also the upcoming 2024 EIPBN Conference Chair. Aimee also serves as co-founder and President of MAEBL Inc, a not-for-profit corporation focused on building and enhancing the EBL community. MAEBL hosts the Meeting for Advanced Electron Beam Lithography each year, live or virtually, in various US academic sites. Prior to her arrival at OSU, Aimee spent five years at TriQuint Semiconductor (now Qorvo) in Dallas, Texas, where she was a member of the EBL group in the Process Engineering Department. She holds a B.S. in Chemistry from The Pennsylvania State University, where she did surface chemistry research with the research groups of Professors Paul Weiss and David Allara. Her current research interests in the Professor Tyler Grassman and Steven A. Ringel groups are in the area of integrated nanostructures within III-V and III-nitride epitaxial materials.



Dr. Gerald Lopez (MAEBL Co-Founder, Board Chair, Treasurer, and Board Member) is the Director of Operations and Business Development at the University of Pennsylvania Singh Center for Nanotechnology. His role creates and executes strategies that articulate the Center's values; establish the Center's operational processes; and facilitate the Center's engagement and collaboration. His professional experience encompasses litho process development and tooling as a former manager at the Singh Center's Quattrone Nanofabrication Facility; technical sales and support in direct-write lithography at GenlSys, Inc.; software engineering at SITA; his former nanotechnology consultancy, Helio Nano, LLC; and his time as a graduate researcher at the Georgia Institute of Technology. Gerald is the Board Chair and co-founder of the Meeting for Advanced Electron Beam Lithography (MAEBL). Moreover, he serves in the organization and planning leadership for the International Conference on Electron, Ion and Photon Beam Technology and Nanofabrication (EIPBN) and was the 2021 Conference Chair. He is passionate about education, mentorship, and connecting the next generation to nano-enabled opportunities. Gerald received his Ph.D. and M.S. in Electrical & Computer Engineering from the Georgia Institute of Technology (under the advisement of Dr. James D. Meindl and Jeffrey A. Davis) and his B.S. in Computer Engineering cum laude from the University of Maryland, Baltimore County.



Mark K Mondol (MAEBL Vice President and Board Member) joined Prof. Hank Smith's NanoStructures Lab at MIT in 1990. He soon took over operation of a 50keV, LaB6 tool donated by IBM's e-beam lithography research group. In 2000 he received the first Raith 150 tool in North America, making 2 tools available to MIT e-beam lithographers. In 2012 MIT purchased an Elionix 125 keV tool and a decade later a 50 keV tool, which he now manages for MIT.nano. Mark has given many talks and helped develop a wide array of e-beam fabrication processes. He has trained over 350 e-beam lithography users and helped guide them through their research. His previous experience with Ringling Bros. circus proved very useful in these tasks.



Mason Risley (MAEBL Secretary and Board Member) is an R&D Process Engineer with 10 years of experience in the semiconductor field having worked in both industry and academia. Specializing in device fabrication across the myriad of processing techniques involved with semiconductor manufacturing, Mason was the primary tool owner for the Carnegie Mellon University Nanofab E-Beam Lithography system between 2016-2020. Mason has been involved with MAEBL since its first meeting in spring of 2017 and joined the MAEBL board in 2021. Mason earned a Bachelor of Science in Chemical Engineering at the New Mexico Institute of Mining and Technology and a Master of Science in Chemical Engineering at the Georgia Institute of Technology.



Dr. Guy A. DeRose (MAEBL Board Member) came to Caltech from the Air Force Research Laboratory in 1994 and is now the Associate Director of Technical Operations for the Kavli Nanoscience Institute (KNI). A core mission of the KNI is to push the state-of-the-art beyond current capabilities in nanofabrication. A large part of his daily activity includes managing two Raith EBPG electron beam lithography systems, from routine operations to training users, and coordinating maintenance with other technical staff and vendors. His research includes using electron-beam lithography and anisotropic etching to fabricate semiconductor lasers and nanophotonic systems and is pushing the envelope on new resist capabilities that go well beyond traditional polymer materials. Prior to joining Caltech, Guy earned his B.S. in Physics from Indiana University of Pennsylvania and M.S. and Ph.D. degrees in Physics from Case Western Reserve University. His graduate research used X-ray absorption techniques with synchrotron radiation to study the mechanical properties of thin metal films. Guy joined the MAEBL Board in 2020, and is very excited to be hosting the event in-person at Caltech in September 2022.



Justin C. Wirth, PhD, (MAEBL Board Member) is a Research Engineer in the Birck Nanotechnology Center at Purdue University. He maintains and operates the North American demonstration JEOL JBX-8100FS, and over the last 10 years has also previously used Raith EBPG 5200 and Leica/Vistec/Raith VB6 EBL systems. His current work focuses on making EBL knowledge more openly accessible, enabling higher throughput exposures. and exploring safer developers.

MAEBL Community Conduct Expectations

MAEBL is committed to providing a safe and inclusive community environment for professional networking, an open exchange of EBL related experiences and ideas, and mutual learning and education.

In order to maintain a welcoming space and community, the following types of conduct are not tolerated at MAEBL meetings, at gatherings related to MAEBL meetings, or in MABEL community platforms:

- Harassment: unwelcome conduct that undermines a safe and inclusive community environment, especially based on factors of a person's identity unrelated to MAEBL's mission.
- Sexual harassment: unwelcome romantic or sexual advances, behavior, or comments.
- Discrimination: exclusion of a person based on factors of a person's identity unrelated to MAEBL's mission.
- Retaliation: punitive treatment of a person for bringing attention, in good faith, to conduct that undermine a safe and inclusive community environment.

Acts of harassment, sexual harassment, discrimination, or retaliation are encouraged to be reported to a member (or members) of the MAEBL board, will be taken seriously, and will be investigated.

Substantiated instances of conduct contrary to community expectations will be handled by members of the MAEBL board addressing and challenging the conduct with the transgressing person and explaining conduct expectations. It is expected that the person will change future conduct to be mindful of and consistent with community expectations.

Repeated, bad faith, or exceptionally serious conduct may necessitate exclusion from the community for an appropriate period of time. Bad faith claims are themselves considered to be harassment; good faith claims that are not substantiated are not considered harassment and are protected from retaliation.

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MEETING FOR ADVANCED E-BEAM LITHOGRAPHY